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Table of Contents

Section I – Regular Papers

These papers were submitted to the Conference Review Committee and appear in the RADECS 2017 Conference Papers, in IEEE Xplore (Conference Section, RADECS 2017).

SESSION A: In-Orbit Low-Cost Radiation Studies

SESSION B: Radiation effects in Optoelectronics and Photonics devices and ICs

SESSION C: Basic mechanisms of radiation effects

SESSION D: Radiation Effects on Materials

SESSION E: Single Event Transients and Laser testing

SESSION ET and ROUNDTABLE: Radiation Tests and Components Qualification

SESSION F: Radiation Effects in Devices and ICs

SESSION G: Radiation Hardening by Design

SESSION H: Single Event Effects in Devices and ICs

SESSION I: Single Event Effects Mechanisms and Modelling

SESSION J: Facilities and Dosimetry

SESSION K: Radiation Hardness Assurance at devices and system level

SESSION L: Radiation Environments (space, atmospheric, terrestrial and accelerators)

SESSION M - Analog And Mixed-Signal Integrated Circuits For Use in Space Applications and Radiation Environments (AMICSA)

REDW Radiation Effect Data Workshop Poster Session

Section II – Selected Papers - N/A

These papers were submitted by their Authors to IEEE Transactions on Nuclear Science and appear in IEEE Trans. On Nucl. Sci., vol 65, Number 8, August 2018. They also can be found in IEEEXplore (IEEE Trans. on Nucl. Sci, RADECS 2017 special issue).

SESSION A: In-Orbit Low-Cost Radiation Studies

AT-1 **System Level Radiation Characterization of a 1U CubeSat Based on CERN Radiation Monitoring Technology**
R. Secondo, R. García Alía, P. Peronnard, M. Brugger, A. Masi, S. Danzeca, A. Merlenghi, E. Chesta, J. R. Vaillè, M. Bernard, and L. Dusseau
DOI: 10.1109/TNS.2018.2797319

SESSION B: Radiation effects in Optoelectronics and Photonics devices and ICs

BT-1 **X-Ray, Proton and Electron Radiation Effects on Type I Fiber Bragg Gratings**
T. Blanchet, A. Morana, T. Allanche, C. Sabatier, I. Reghioua, E. Marin, A. Boukenter, Y. Ouerdane, P. Paillet, M. Gaillardin, O. Duhamel, C. Marcandella, M. C. Trinczek, G. Assaillit, G. Auriel, D. Aubert, G. Laffont, and S. Girard
DOI: 10.1109/TNS.2018.2823771

BT-2 **A Method to Separate Proton Damage in LED and Phototransistor of Optocouplers**
F. Irom, L. D. Edmonds, G. R. Allen, and B. G. Rax
DOI: 10.1109/TNS.2018.2819960

BT-3 **Investigation of the Influence of Temperature and Annealing on the Radiation Hardness of Silicon Mach–Zehnder Modulators**
A. Kraxner, S. Detraz, L. Olantera, C. Scarcella, C. Sigaud, C. Soos, J. Troska, and F. Vasey
DOI: 10.1109/TNS.2018.2823863

BT-4 **Radiation-Induced Defects in 8T-CMOS Global Shutter Image Sensor for Space Applications**
A. Le Roch, C. Virmontois, V. Goiffon, L. Tauzième, J.-M. Belloir, C. Durnez, and P. Magnan
DOI: 10.1109/TNS.2018.2820385

BT-5 **6-MeV Electron Exposure Effects on OFDR-Based Distributed Fiber-Based Sensors**
C. Sabatier, S. Rizzolo, A. Morana, T. Allanche, T. Robin, B. Cadier, P. Paillet, M. Gaillardin, O. Duhamel, C. Marcandella, D. Aubert, G. Assaillit, G. Auriel, A. Boukenter, Y. Ouerdane, L. Mescia, E. Marin, and S. Girard
DOI: 10.1109/TNS.2018.2804663

BT-6 **Dependence of the Voids-Fiber Bragg Grating Radiation Response on Temperature, Dose, and Dose Rate**
A. Morana, S. Girard, E. Marin, M. Lancry, J. Grelin, C. Marcandella, P. Paillet, A. Boukenter, and Y. Ouerdane
DOI: 10.1109/TNS.2017.2778882

BT-7 R**andom Telegraph Signal in Proton Irradiated Single-Photon Avalanche Diodes**
F. Di Capua, M. Campajola, L. Campajola, C. Nappi, E. Sarnelli, L. Gasparini, and H. Xu
DOI: 10.1109/TNS.2018.2814823

SESSION C: Basic mechanisms of radiation effects

CT-1 **Heavy Ion, Proton, and Neutron Charge Deposition Analyses in Several Semiconductor Materials**
Z. Wu and S. Chen
DOI: 10.1109/TNS.2018.2834962

CT-2 **Dose-Rate Sensitivity of 65-nm MOSFETs Exposed to Ultrahigh Doses**
G. Borghello, F. Faccio, E. Lerario, S. Michelis, S. Kulis, D. M. Fleetwood, R. D. Schrimpf, S. Gerardin, A. Paccagnella, and S. Bonaldo
DOI: 10.1109/TNS.2018.2828142

CT-3 **Improved Model for Excess Base Current in Irradiated Lateral p-n-p Bipolar Junction Transistors**
B. S. Tolleson, P. C. Adell, B. Rax, H. J. Barnaby, A. Privat, X. Han, A. Mahmud, and I. Livingston
DOI: 10.1109/TNS.2018.2829110

CT-4 **Hydrogen Soaking, Displacement Damage Effects, and Charge Yield in Gated Lateral Bipolar Junction Transistors**
Xingji Li, Jianqun Yang, Daniel M. Fleetwood, Chaoming Liu, Yidan Wei, H. J. Barnaby, and K. F. Galloway
DOI: 10.1109/TNS.2018.2837032

SESSION D: Radiation Effects on Materials

DT-1 **Qualification Strategy of New Technologies for Safety Instrumentation in Harsh Radiation Environments**
C. Zinoni, L. Janvier, and B. Symoens
DOI: 10.1109/TNS.2018.2810448

DT-2 **Ni-Ion and γ -Ray Irradiated Silica-Based Glasses Characterized by Luminescence and Raman Spectroscopies**
A. Alessi, S. Girard, M. Raine, M. Fanetti, D. Di Francesca, L. Martin-Samos, I. Reghioua, M. Gaillardin, N. Richard, P. Paillet, M. Valant, A. Boukenter, and Y. Ouerdane
DOI: 10.1109/TNS.2017.2778884

DT-3 **Growth and Decay Kinetics of Radiation-Induced Attenuation in Bulk Optical Materials**
S. Girard, T. Allanche, P. Paillet, V. Goiffon, M. Van Uffelen, L. Mont-Casellas, C. Muller, A. Boukenter, Y. Ouerdane, and W. De Cock
DOI: 10.1109/TNS.2017.2778318

DT-3 **Degradation of KNN-Based Lead-Free Piezoelectric Material under Gamma Irradiation**
G. Dai, Y. Du, Q. Zhou, L. Zhong, X. Sun, K. Wang, and J. Zhang
DOI: 10.1109/TNS.2018.2817494

SESSION E: Single Event Transients and Laser testing

ET-1 **Single Events Induced By Heavy Ions and Laser Pulses in Silicon Schottky Diodes**
M. Mauguet, D. Lagarde, F. Widmer, N. Chatry, X. Marie, E. Lorfevre, F. Bezerra, R. Marec, and P. Calvel
DOI: 10.1109/TNS.2018.2813096

ET-2 **Effect of Transistor Variants on Single-Event Transients at the 14-/16-nm Bulk FinFET Technology Generation**
R. C. Harrington, J. A. Maharrey, J. S. Kauppila, P. Nsengiyumva, D. R. Ball, T. D. Haeffner, E. X. Zhang, B. L. Bhuva, and L. W. Massengill
DOI: 10.1109/TNS.2018.2843260

ET-3 **Experimental Validation of an Equivalent LET Approach for Correlating Heavy-Ion and Laser-Induced Charge Deposition**
J. M. Hales, A. Khachatrian, S. Buchner, N. J.-H. Roche, J. Warner, Z. E. Fleetwood, A. Ildefonso, J. D. Cressler, V. Ferlet-Cavrois, and D. McMorrow
DOI: 10.1109/TNS.2018.2828332

ET-4 **Experimental Investigation of the Joint Influence of Reduced Supply Voltage and Charge Sharing on Single-Event Transient Waveforms in 65-nm Triple-Well CMOS**
M. Mitrovic, M. Hofbauer, K.-O. Voss, and H. Zimmermann
DOI: 10.1109/TNS.2018.2823273

SESSION F: Radiation Effects in Devices and ICs

FT-1 **Total Ionizing Dose Response and Annealing Behavior of Bulk nFinFETs with ON-State Bias Irradiation**
L. Yang, Q. Zhang, Y. Huang, Z. Zheng, B. Li, B. Li, X. Zhang, H. Zhu, H. Yin, Q. Guo, J. Luo, and Z. Han
DOI: 10.1109/TNS.2018.2827675

FT-2 **An Effective Method to Compensate Total Ionizing Dose-Induced Degradation on Double-SOI Structure**
Y. Huang, B. Li, X. Zhao, Z. Zheng, J. Gao, G. Zhang, B. Li, G. Zhang, K. Tang, Z. Han, and J. Luo
DOI: 10.1109/TNS.2018.2824402

FT-3 **The Increased Single-Event Upset Sensitivity of 65-nm DICE SRAM Induced by Total Ionizing Dose**
Q. Zheng, J. Cui, W. Lu, H. Guo, J. Liu, X. Yu, Y. Wei, L. Wang, J. Liu, C. He, and Q. Guo
DOI: 10.1109/TNS.2018.2816583

FT-4 **TID Response of pMOS Nanowire Field-Effect Transistors: Geometry and Bias Dependence**
J. Riffaud, M. Gaillardin, C. Marcandella, N. Richard, O. Duhamel, M. Martinez, M. Raine, P. Paillet, T. Lagutere, F. Andrieu, S. Barraud, M. Vinet, and O. Faynot
DOI: 10.1109/TNS.2018.2850531

FT-5 **Radiation Tolerance of Proton-Irradiated LGADs**
S. Otero Ugobono, M. Carulla, M. Centis Vignali, M. Fernández García, C. Gallrapp, S. Hidalgo Villena, I. Mateu, M. Moll, G. Pellegrini, and I. Vila
DOI: 10.1109/TNS.2018.2826725

FT-6 **X-Ray and Proton Radiation Effects on 40 nm CMOS Physically Unclonable Function Devices**
P. F. Wang, E. X. Zhang, K. H. Chuang, W. Liao, H. Gong, P. Wang, C. N. Arutt, K. Ni, M. W. McCurdy, I. Verbauwhede, E. Bury, D. Linten, D. M. Fleetwood, R. D. Schrimpf, and R. A. Reed
DOI: 10.1109/TNS.2017.2789160

SESSION G: Radiation Hardening by Design

GT-1 **Radiation-Hardened Flip-Flops with Low-Delay Overhead Using pMOS Pass-Transistors to Suppress SET Pulses in a 65-nm FDSOI Process**
K. Yamada, H. Maruoka, J. Furuta, and K. Kobayashi
DOI: 10.1109/TNS.2018.2826726

GT-2 **Lockstep Dual-Core ARM A9: Implementation and Resilience Analysis Under Heavy Ion-Induced Soft Errors**
Á. B. de Oliveira, G. S. Rodrigues, F. L. Kastensmidt, N. Added, E. L. A. Macchione, V. A. P. Aguiar, N. H. Medina, and M. A. G. Silveira
DOI: 10.1109/TNS.2018.2852606

GT-3 **Power-Aware SE Analysis of Different FF Designs at the 14-/16-nm Bulk FinFET CMOS Technology Node**
H. Jiang, H. Zhang, I. Chatterjee, J. S. Kauppila, B. L. Bhuva, and L. W. Massengill
DOI: 10.1109/TNS.2018.2831002

GT-4 **Dual-Interlocked Logic for Single-Event Transient Mitigation**
J. A. Maharrey, J. S. Kauppila, R. C. Harrington, P. Nsengiyumva, D. R. Ball, T. D. Haeffner, E. X. Zhang, B. L. Bhuva, W. T. Holman, and L. W. Massengill
DOI: 10.1109/TNS.2017.2783239

GT-5 **On the Efficacy of ECC and the Benefits of FinFET Transistor Layout for GPU Reliability**
C. Lunardi, F. Previlon, D. Kaeli, and P. Rech
DOI: 10.1109/TNS.2018.2823786

SESSION H: Single Event Effects in Devices and ICs

HT-1 **Impact of D-Flip-Flop Architectures and Designs on Single-Event Upset Induced by Heavy Ions**
L. Artola, G. Hubert, S. Ducret, J. Mekki, A. Al Youssef, and N. Ricard
DOI: 10.1109/TNS.2018.2800742

HT-2 **Radiation Effects on Deep Submicrometer SRAM-Based FPGAs under the CERN Mixed-Field Radiation Environment**
G. Tsiligiannis, S. Danzeca, R. García Alía, A. Infantino, A. Lesea, M. Brugger, A. Masi, S. Gilardoni, and F. Saigné
DOI: 10.1109/TNS.2018.2806450

HT-3 **Analysis of Temporal Masking Effects on Master- and Slave-Type Flip-Flop SEUs and Related Applications**
R. M. Chen, N. N. Mahatme, Z. J. Diggins, L. Wang, E. X. Zhang, Y. P. Chen, Y. N. Liu, B. Narasimham, A. F. Witulski, B. L. Bhuva, and D. M. Fleetwood
DOI: 10.1109/TNS.2018.2823385

HT-4 **Negative and Positive Muon-Induced Single Event Upsets in 65-nm UTBB SOI SRAMs**
S. Manabe, Y. Watanabe, W. Liao, M. Hashimoto, K. Nakano, H. Sato, T. Kin, S.-I. Abe, K. Hamada, M. Tampo, and Y. Miyake
DOI: 10.1109/TNS.2018.2839704

HT-5 **Mechanisms of Electron-Induced Single-Event Upsets in Medical and Experimental Linacs**
M. Tali, R. García Alía, M. Brugger, V. Ferlet-Cavrois, R. Corsini, W. Farabolini, A. Javanainen, M. Kastriotou, H. Kettunen, G. Santin, C. Boatella Polo, G. Tsiligiannis, S. Danzeca, and A. Virtanen
DOI: 10.1109/TNS.2018.2843388

HT-6 **Single-Event Effects in the Peripheral Circuitry of a Commercial Ferroelectric Random Access Memory**
L. Bosser, V. Gupta, A. Javanainen, G. Tsiligiannis, S. D. LaLumondiere, D. Brewe, V. Ferlet-Cavrois, H. Puchner, H. Kettunen, T. Gil, F. Wrobel, F. Saigné, A. Virtanen, and L. Dilillo
DOI: 10.1109/TNS.2018.2797543

HT-7 **Evaluation of the Suitability of NEON SIMD Microprocessor Extensions Under Proton Irradiation**
A. Lindoso, M. García-Valderas, L. Entrena, Y. Morilla, and P. Martín-Holgado
DOI: 10.1109/TNS.2018.2823540

HT-8 **Effects of Total-Ionizing-Dose Irradiation on Single-Event Response for Flip-Flop Designs at a 14-/16-nm Bulk FinFET Technology Node**
H. Zhang, H. Jiang, X. Fan, J. S. Kauppila, I. Chatterjee, B. L. Bhuva, and L. W. Massengill
DOI: 10.1109/TNS.2017.2781622

HT-9 **SEU Characterization of Three Successive Generations of COTS SRAMs at Ultralow Bias Voltage to 14.2-MeV Neutrons**
J. A. Clemente, G. Hubert, J. Fraire, F. J. Franco, F. Villa, S. Rey, M. Baylac, H. Puchner, H. Mecha, and R. Velazco
DOI: 10.1109/TNS.2018.2800905

HT-10 **SEE Error-Rate Evaluation of an Application Implemented in COTS Multicore/ Many-Core Processors**
P. Ramos, V. Vargas, M. Baylac, N.-E. Zergainoh, and R. Velazco
DOI: 10.1109/TNS.2018.2838526

SESSION I: Single Event Effects Mechanisms and Modelling

IT-1 **Physical Mechanisms Inducing Electron Single-Event Upset**
P. Caron, C. Inguimbert, L. Artola, N. Chatry, N. Sukhaseum, R. Ecoffet and F. Bezerra
DOI: 10.1109/TNS.2018.2819421

IT-2 **Impact of Heavy Ion Energy on Charge Yield in Silicon Dioxide**
V. V. Emeliyanov, A. S. Vatuev, and R. G. Useinov
DOI: 10.1109/TNS.2018.2813669

IT-3 **The Impact of Multiple-Cell Charge Generation on Multiple-Cell Upset in a 20-nm Bulk SRAM**
T. Kato, T. Yamazaki, K. Maruyama, T. Soeda, H. Itsuji, D. Kobayashi, K. Hirose, and H. Matsuyama
DOI: 10.1109/TNS.2018.2830781

IT-4 **Single-Event Burnout Mechanisms in SiC Power MOSFETs**
F. Witulski, D. R. Ball, K. F. Galloway, A. Javanainen, J.-M. Lauenstein, A. L. Sternberg, and R. D. Schrimpf
DOI: 10.1109/TNS.2018.2849405

IT-5 **Single-Event Damage Observed in GaN-on-Si HEMTs for Power Control Applications**
E. Mizuta, S. Kuboyama, Y. Nakada, A. Takeyama, T. Ohshima, Y. Iwata, and K. Suzuki
DOI: 10.1109/TNS.2018.2819990

IT-6 **Analysis and Modeling of the Charge Collection Mechanism in 28-nm FD-SOI**
V. Correas, I. Nofal, J. Cerba, F. Monsieur, G. Gasiot, D. Alexandrescu, P. Roche, and R. Gonella
DOI: 10.1109/TNS.2018.2828162

IT-7 **Measurement and Mechanism Investigation of Negative and Positive Muon-Induced Upsets in 65-nm Bulk SRAMs**
W. Liao, M. Hashimoto, S. Manabe, Y. Watanabe, S.-I. Abe, K. Nakano, H. Sato, T. Kin, K. Hamada, M. Tampo, and Y. Miyake
DOI: 10.1109/TNS.2018.2825469

IT-8 **Circuit-Level Layout-Aware Modeling of Single-Event Effects in 65-nm CMOS ICs**
A. O. Balbekov, M. S. Gorbunov, and G. I. Zebrev
DOI: 10.1109/TNS.2018.2802205

IT-9 **Analysis of Temporal Masking Effects on Master- and Slave-Type Flip-Flop SEUs and Related Applications**
R. M. Chen, N. N. Mahatme, Z. J. Diggins, L. Wang, E. X. Zhang, Y. P. Chen, Y. N. Liu, B. Narasimham, A. F. Witulski, B. L. Bhuva, and D. M. Fleetwood
DOI: 10.1109/TNS.2018.2823385

SESSION J: Facilities and Dosimetry

JT-1 **Radioluminescence and Optically Stimulated Luminescence Responses of a Cerium-Doped Sol-Gel Silica Glass under X-Ray Beam Irradiation**
N. Al Helou, H. El Hamzaoui, B. Capoen, G. Bouwmans, A. Cassez, Y. Ouerdane, A. Boukenter, S. Girard, G. Chadeyron, R. Mahiou, and M. Bouazaoui
DOI: 10.1109/TNS.2017.2787039

JT-2 **Atmospheric-Like Neutron Attenuation during Accelerated Neutron Testing With Multiple Printed Circuit Boards**
C. Cazzaniga, B. Bhuva, M. Bagatin, S. Gerardin, N. Marchese, and C. D. Frost
DOI: 10.1109/TNS.2018.2825644

JT-3 **Distributed Optical Fiber Radiation Sensing in the Proton Synchrotron Booster at CERN**
D. Di Francesca, I. Toccafondo, G. Li Vecchi, S. Calderini, S. Girard, A. Alessi, R. Ferraro, S. Danzeca, Y. Kadi, and M. Brugger
DOI: 10.1109/TNS.2018.2818760

JT-4 **ReadMON: A Portable Readout System for the CERN PH-RADMON Sensors**
I. Mateu, M. Glaser, G. Gorine, M. Moll, G. Pezzullo, and F. Ravotti
DOI: 10.1109/TNS.2017.2784684

JT-5 **Ultrahigh Fluence Radiation Monitoring Technology for the Future Circular Collider at CERN**
G. Gorine, G. Pezzullo, I. Mandic, A. Jazbec, L. Snoj, M. Capeans, M. Moll, D. Bouvet, F. Ravotti, and J.-M. Sallese
DOI: 10.1109/TNS.2018.2797540

JT-6 **Thermal Neutron SRAM Detector Characterization at the CERN Mixed-Field Facility, CHARM**
C. Cangialosi, S. Danzeca, M. Brucoli, M. Brugger, and A. Masi
DOI: 10.1109/TNS.2018.2829631

JT-7 **SEE Testing in the 24-GeV Proton Beam at the CHARM Facility**
R. García Alía, M. Brugger, M. Cecchetto, F. Cerutti, S. Danzeca, M. Delrieux, M. Kastriotou, M. Tali, and S. Uznanski
DOI: 10.1109/TNS.2018.2831786

SESSION K: Radiation Hardness Assurance at devices and system level

KT-1 **Reliability–Performance Analysis of Hardware and Software Co-Designs in SRAM-Based APSoCs**
L. Antunes Tambara, F. L. Kastensmidt, P. Rech, F. Lins, N. H. Medina, N. Added, V. A. P. Aguiar, and M. A. G. Silveira
DOI: 10.1109/TNS.2018.2844250

SESSION L: Radiation Environments (space, atmospheric, terrestrial and accelerators)

LT-1 **In-Flight Dark Current Nonuniformity Used for Space Environment Model Benchmarking**
C. Inguimbert, S. Bourdarie, M. Beaumel, M. C. Ursule, and R. Ecoffet
DOI: 10.1109/TNS.2018.2800903

LT-2 **Electron Environment Characteristics and Internal Charging Evaluation for MEO Satellite**
J.-Z. Wang, Y.-Q. Hu, D.-Y. Yu, Z.-B. Cai, and Q.-X. Zhang
DOI: 10.1109/TNS.2018.2792049

LT-3 **High-Energy Electrons in the Inner Zone**
D. Boscher, S. Bourdarie, V. Maget, A. Sicard, G. Rolland, and D. Standarovski
DOI: 10.1109/TNS.2018.2824543

LT-4 **Contribution of Thermal Neutrons to Soft Error Rate**
C. Weulersse, S. Houssany, N. Guibbaud, J. Segura-Ruiz, J. Beaucour, F. Miller, and M. Mazurek
DOI: 10.1109/TNS.2018.2813367

LT-5 **Electrons in GEO Measured With the ESA Multifunctional Spectrometer During the January 2014 SEP**
L. Arruda, P. Gonçalves, F. Carvalho, A. Marques, J. C. Pinto, A. Aguilar, P. Marinho, T. Sousa, H. Evans, and P. Nieminen
DOI: 10.1109/TNS.2018.2854161

LT-6 **Impact of Thermal and Intermediate Energy Neutrons on SRAM SEE Rates in the LHC Accelerator**
M. Cecchetto, R. García Alía, S. Gerardin, M. Brugger, A. Infantino, and S. Danzeca
DOI: 10.1109/TNS.2018.2831786

SESSION M - Analog and Mixed-Signal Integrated Circuits for Use in Space Applications and Radiation Environments (AMICSA)

MT-1 **Design of a Radiation Hardened Power-ON-Reset**
E. López-Morillo, F. R. Palomo, F. Márquez, and F. Muñoz
DOI: 10.1109/TNS.2018.2840326

SECTION SC: SHORT COURSE papers

SC-1 **Evolution of Total Ionizing Dose Effects in MOS Devices with Moore's Law Scaling**
D. M. Fleetwood
DOI: 10.1109/TNS.2017.2786140

SC-2 **Dosimetry Techniques and Radiation Test Facilities for Total Ionizing Dose Testing**
F. Ravotti
DOI: 10.1109/TNS.2018.2829864

SC-3 **Displacement Damage in Silicon Detectors for High Energy Physics**
M. Moll
DOI: 10.1109/TNS.2018.2797540